

SMAF



Features:

- ☐ Metal silicon junction, majority carrier conduction
- ☐ For surface mounted applications
- ☐ Low power loss, high efficiency
- ☐ Fast switching for high efficiency
- ☐ High forward surge current capability
- ☐ For use in low voltage, high frequency inverters



1. Cathode 2. Anode

Absolute Maximum Ratings* (TA=25°C Unless otherwise noted)

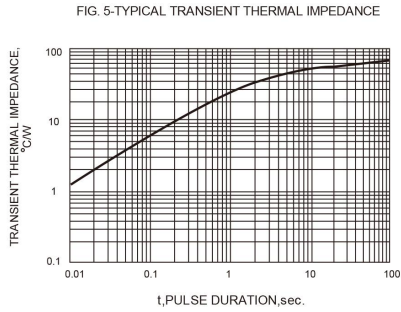
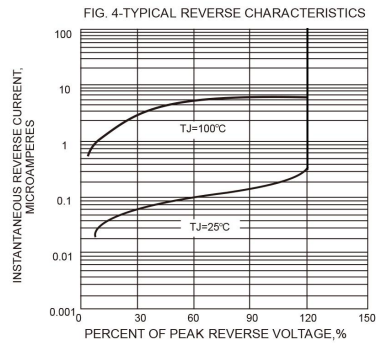
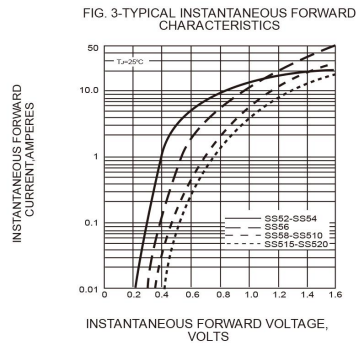
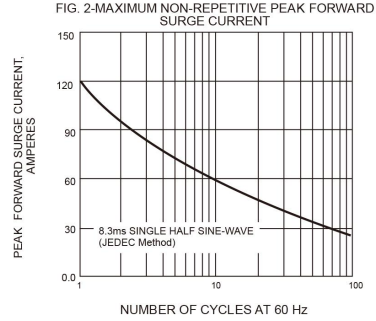
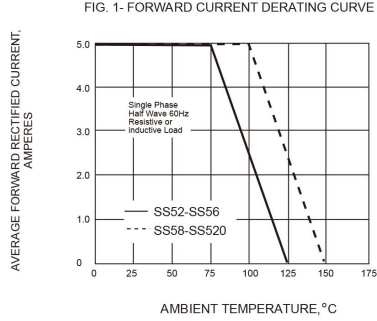
Ratings at 25 °C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz resistive or inductive load, for capacitive load, derate by 20 %

Parameter	Symbols	CH52F	CH54F	CH56F	CH58F	CH510F	CH512F	CH510F	CH520F	Units
Maximum Repetitive Peak Reverse Voltage	V _{RRM}	20	40	60	80	100	120	150	200	V
Maximum RMS voltage	V _{RMS}	14	28	42	56	70	84	105	140	V
Maximum DC Blocking Voltage	V _{DC}	20	40	60	80	100	120	150	200	V
Maximum Average Forward Rectified Current	I _{F(AV)}	5.0								A
Peak Forward Surge Current,8.3ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I _{FSM}	120								A
Max Instantaneous Forward Voltage at 5A	V _F	0.52		0.65	0.80			0.90		V
Maximum DC Reverse Current T _a = 25°C at Rated DC Reverse Voltage T _a =100°C	I _R	0.3 10			0.2 5			0.1 2		mA
Typical Junction Capacitance ⁽¹⁾	C _j	500		300						pF
Typical Thermal Resistance ⁽²⁾	R _{θJA}	45								°C/W
Operating Junction Temperature Range	T _j	-55 ~ +125				-55 ~ +150				°C
Storage Temperature Range	T _{stg}	-55 ~ +150								°C

(1) Measured at 1 MHz and applied reverse voltage of 4 V.D.C

(2) P.C.B. mounted with 2.0" X 2.0" (5 X 5 cm) copper pad areas.

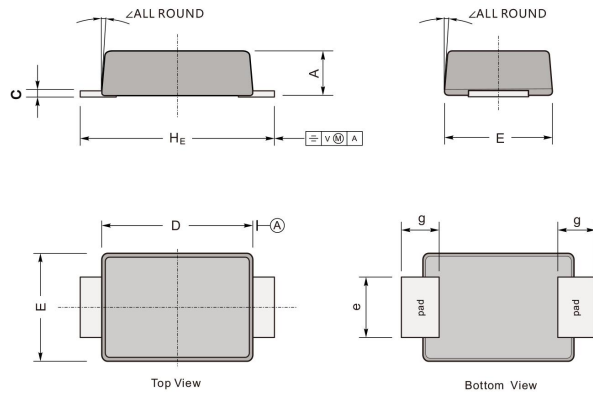
Typical Characteristics



Package Dimension

SMAF

Unit: mm



UNIT		A	C	D	E	e	g	H _E	∠
mm	max	1.2	0.20	3.7	2.7	1.6	1.2	4.9	7°
	min	0.9	0.12	3.3	2.4	1.3	0.8	4.4	
mil	max	47	7.9	146	106	63	47	193	
	min	35	4.7	130	94	51	31	173	

The recommended mounting pad size

